



《风光欣》技术资料

S9013

NPN EPITAXIAL SILICON TRANSISTOR

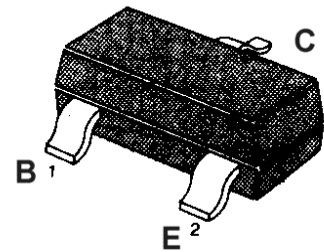
*High Collector Current($I_{cm} = 500mA$)

*Complementary to **S9012**

ABSOLUTE MAXIMUM RATINGS($T_a = 25$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	40	V
Collector-Emitter Voltage	V_{CE0}	20	V
Emitter -Base Voltage	V_{EB0}	5	V
Collector Current	I_{cm}	500	mA
Collector Dissipation	P_{cm}	225	mW
Junction Temperature	T_j	150	

SOT-23



ELECTRICAL CHARACTERISTICS($T_a = 25$)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Bare Breakdown Volitage	BV_{CB0}	$I_c = 100 \mu A, I_E = 0$	40			V
Collector-Emitter Breakdown Volitage	BV_{CE0}	$I_c = 1mA, I_B = 0$	20			V
Emitter-Base Breakdown Volitage	BV_{EB0}	$I_E = 100 \mu A, I_c = 0$	5			V
Collector-Cut-off Current	I_{CB0}	$V_{CB} = 40V, I_E = 0$			100	nA
Emitter Cut-off Current	I_{EB0}	$V_{EB} = 3V, I_c = 0$			100	nA
DC Current Gain	h_{FE1}	$V_{CE} = 1V, I_c = 50mA$	64	120	300	
	h_{FE2}	$V_{CE} = 1V, I_c = 500mA$	30			
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_c = 500mA, I_B = 50mA$		0.16	0.6	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_c = 500mA, I_B = 50mA$		0.91	1.2	V
Base-Emitter Voltage	$V_{BE(on)}$	$V_{CE} = 1V, I_c = 10mA$	0.6	0.67	0.7	V